







## **Application**

Laser Projectorpment Measurig equi

# **Property**

Wavelength  $\lambda$  = 980 nm Output Power = 200 mW Package Type =  $\phi$  5.6mm

### Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer. Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

## Red Laser Diode Key features

#### Absolute Maximum Rating at Tc=25℃

Items	Symbols	Symbols Values	
Operating Current power	P <sub>o</sub>	200	mW
Reverse Voltage	$V_{R}$	2	V
Operating Temperature	$T_{case}$	-10~+40	$^{\circ}\!\mathbb{C}$
Storage Temperature	$T_s$	-40~+85	$^{\circ}\! \mathbb{C}$



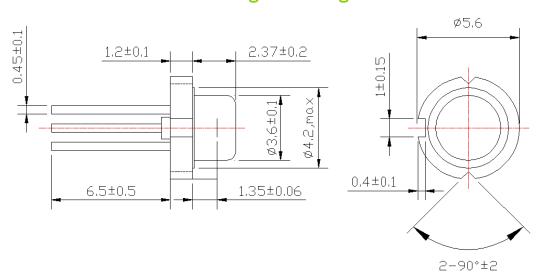


# 980nm RED Laser Diode

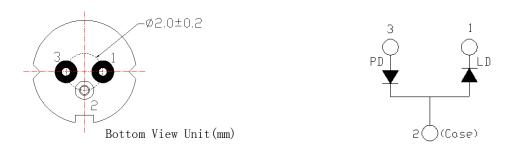
#### Electrical and Optical Characteristics at Tc=25℃

ltem	Symbols	Min	Тур.	Max.	Unit	Condition
Threshold Current	$I_{th}$	-	65	80	mA	-
Operating Current	$I_{op}$	-	330	380	mA	Po=200mW
Operating Voltage	$V_{op}$	1	1.5	2.1	V	Po=200mW
Peak Wavelength	λр	970	980	990	nm	Po=200mW
Beam Divergence (FWHM)	$\theta_{/\!\!/}$	-	9	-	deg	Po=200mW
Beam Divergence (FWHM)	$ heta \perp$	27	30	37	deg	Po=200mW
Monitor Current	I <sub>m</sub>	0.5	0.75	-	mA	Po=200mW

# **Package Drawing**



## **ELECTRICAL CONNECTION**



Specifications are subject to change without notice.



